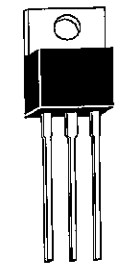
HMJE2955T

PNP EPITAXIAL PLANAR TRANSISTOR



TO-220

Description

The HMJE2955T is designed for general purpose of amplifier and switching applications.

Absolute Maximum Ratings (T_A=25°C)

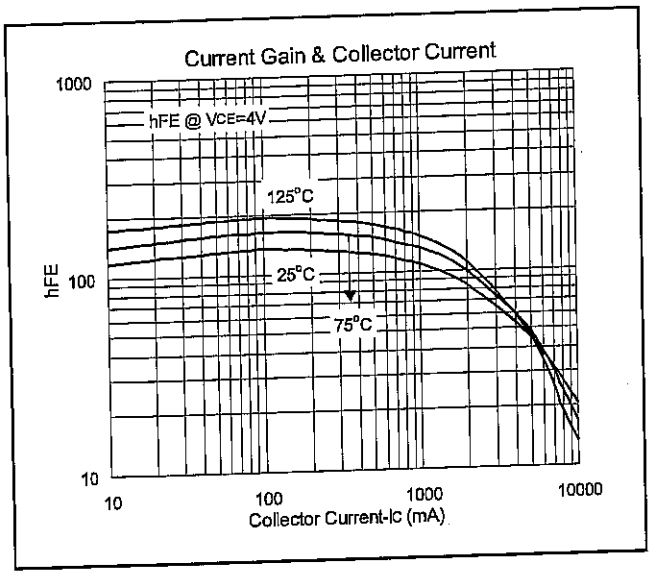
- Maximum Temperatures
  - Storage Temperature ..... -55 ~ +150 °C
  - Junction Temperature ..... 150 °C Maximum
- Maximum Power Dissipation
  - Total Power Dissipation (T_C=25°C) ..... 75 W
  - Total Power Dissipation (T_A=25°C) ..... 0.6 W
- Maximum Voltages and Currents
  - BV_{CBO} Collector to Base Voltage ..... -70 V
  - BV_{CEO} Collector to Emitter Voltage ..... -60 V
  - BV_{EBO} Emitter to Base Voltage ..... -5 V
  - I_C Collector Current ..... -10 A
  - I_B Base Current ..... -6 A

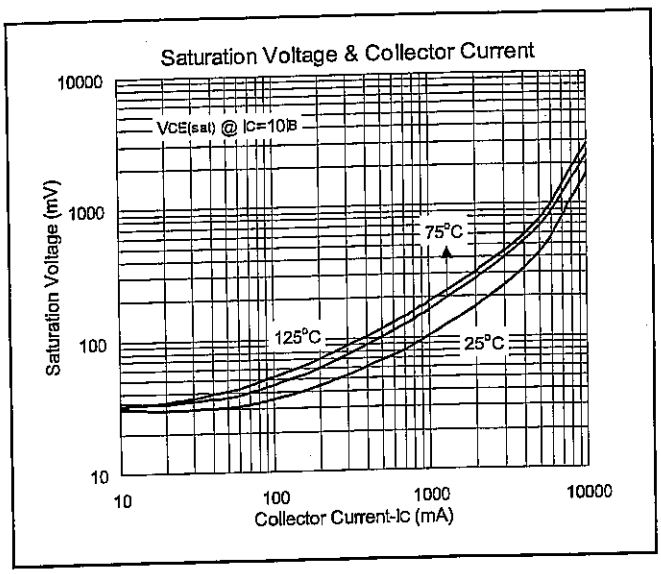
Electrical Characteristics (T_A=25°C)

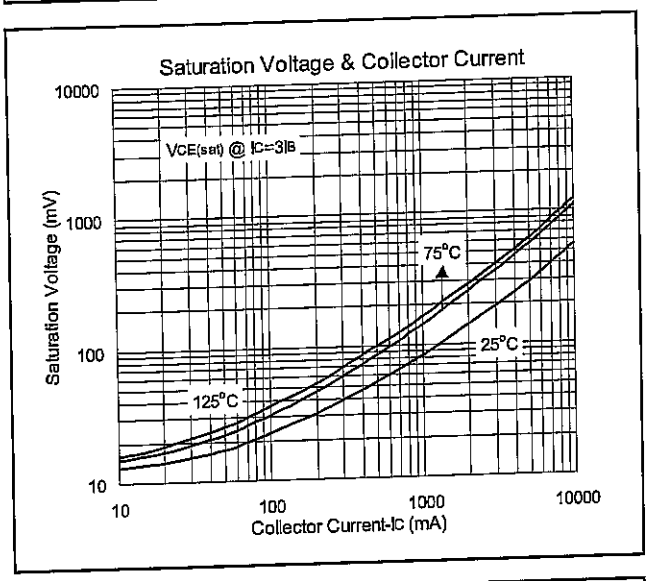
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-70	-	-	V	I_C=-10mA, I_E=0
BV_{CEO}	-60	-	-	V	I_C=-200mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-1mA, I_C=0
I_{CBO}	-	-	-1	mA	V_{CB}=-70V, I_E=0
I_{CEX}	-	-	-1	mA	V_{CE}=-70V, $V_{EB(off)}$=-1.5V
I_{CEO}	-	-	-700	uA	V_{CE}=-30V, I_B=0
I_{EBO}	-	-	-5	mA	V_{EB}=-5V, I_C=0
*$V_{CE(sat)1}$	-	-	-1.1	V	I_C=-4A, I_B=-400mA
*$V_{CE(sat)2}$	-	-	-8	V	I_C=-10A, I_B=-3.3A
*$V_{BE(on)}$	-	-	-1.8	V	I_C=-4A, V_{CE}=-4V
*h_{FE1}	20	-	100		I_C=-4A, V_{CE}=-4V
*h_{FE2}	5	-	-		I_C=-10A, V_{CE}=-4V
f_T	2	-	-	MHz	V_{CE}=-10V, I_C=-500mA, f=0.5MHz

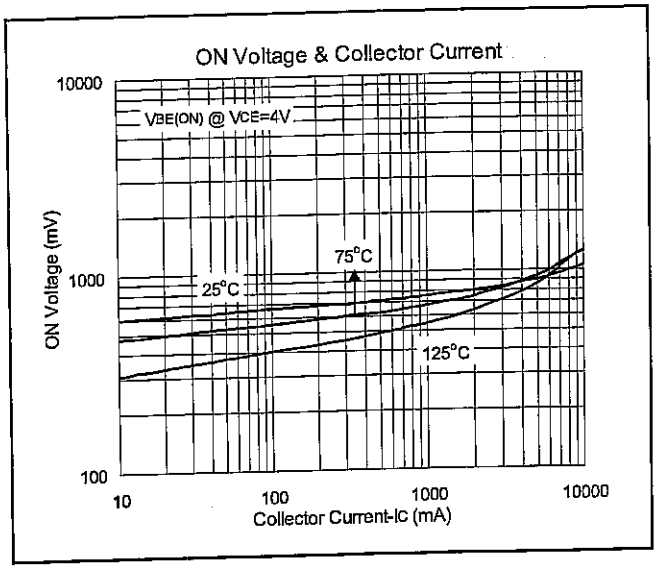
*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

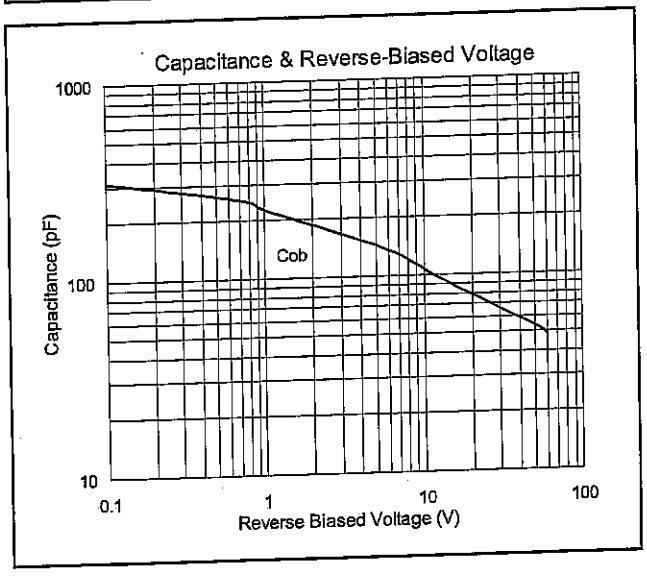
Characteristics Curve

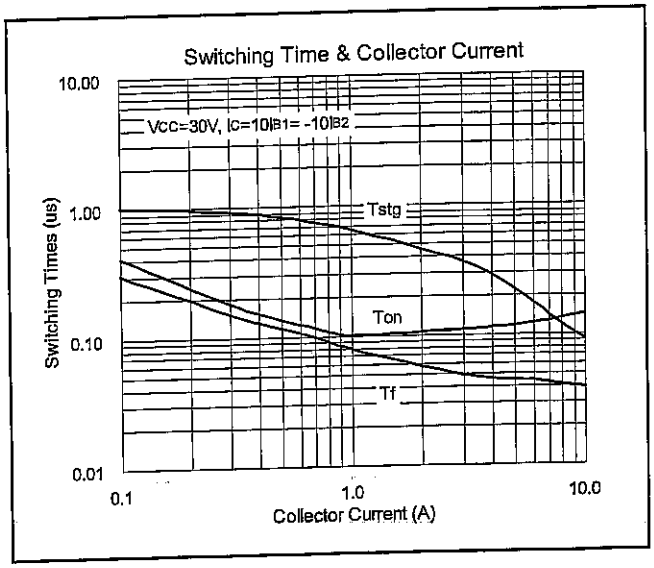


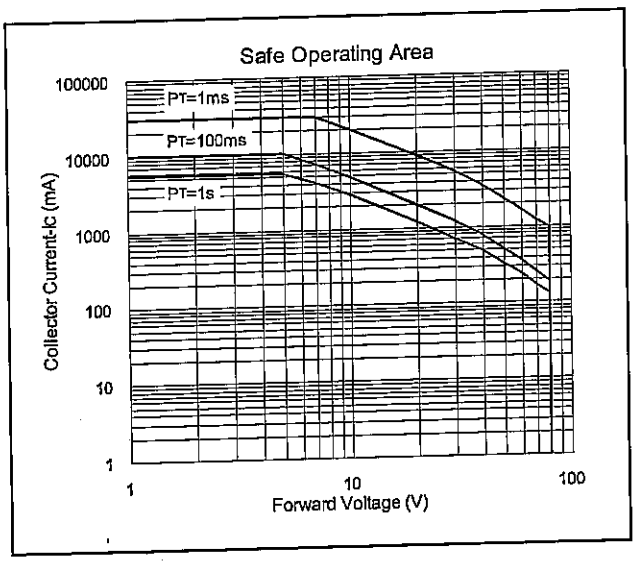




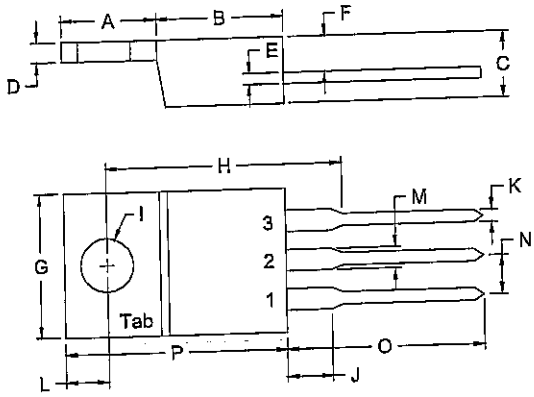






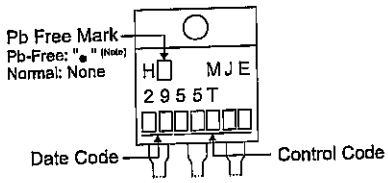

Safe Operating Area
100000
10000
1000
100
10
1
Collector Current-Ic (mA)
PT=1ms
PT=100ms
PT=1s
1
10
100
Forward Voltage (V)

TO-220 Dimension



3-Lead TO-220
Plastic Package
HSMC Package Code: E

Marking:



Note: Green label is used for pb-free packing

Pin Style: 1.Base 2 & Tab.Collector 3.Emitter

Material:
- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	5.58	7.49
B	8.38	8.90
C	4.40	4.70
D	1.15	1.39
E	0.35	0.60
F	2.03	2.92
G	9.66	10.28
H	-	*16.25
I	-	*3.83
J	3.00	4.00
K	0.75	0.95
L	2.54	3.42
M	1.14	1.40
N	-	*2.54
O	12.70	14.27
P	14.48	15.87

*: Typical, Unit: mm

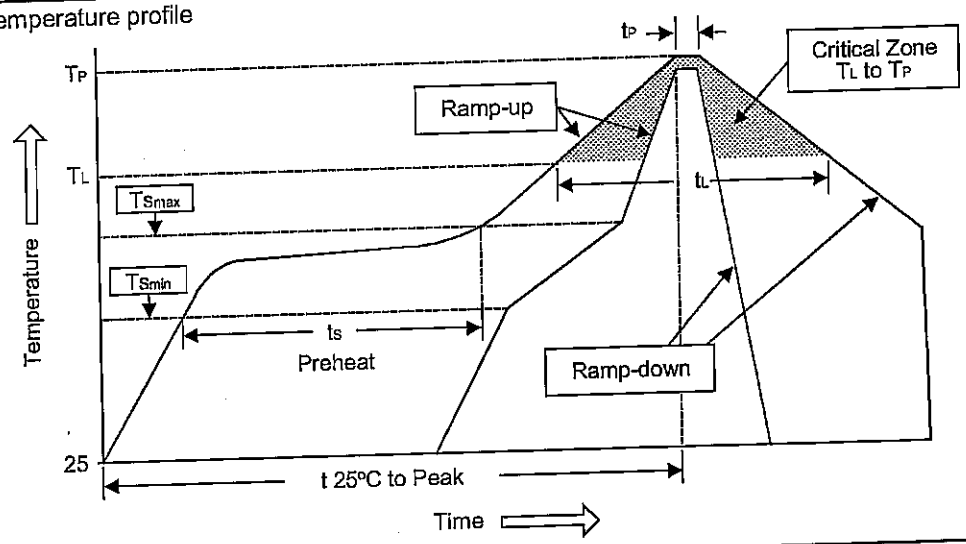
Head Office And Factory:
- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F.,No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
  Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
  Tel: 886-3-5983621~5 Fax: 886-3-5982931

Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%

2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat - Temperature Min (Ts_{min}) - Temperature Max (Ts_{max}) - Time (min to max) (ts)	100°C 150°C 60~120 sec	150°C 200°C 60~180 sec
Tsmax to T_L - Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60~150 sec	217°C 60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec